



GL1S50N06LA4

GL Silicon N-Channel Power MOSFET

General Description

The GL1S50N06LA4 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications. The package form is TO-252, which accords with the RoHS standard.

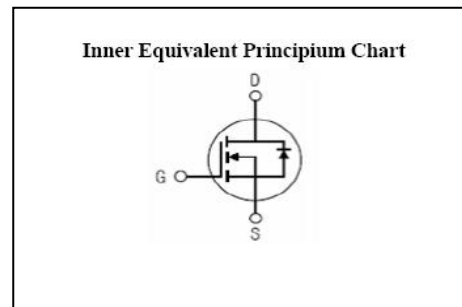
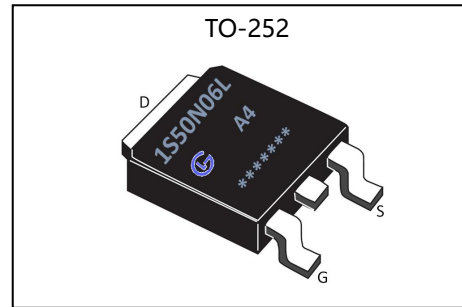
Features

- Fast Switching
- Low Gate Charge and $R_{ds(on)}$
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

V_{DSS}	60	V
I_D	50	A
P_D	85	W
$R_{DS(ON)type}$	13.5	m Ω



Absolute (Tc= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current	50	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	35	A
I_{DM}	Pulsed Drain Current	200	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	300	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	50	mJ
I_{AR}^{a1}	Avalanche Current	28	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	85	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, -55 to 175	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device



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Electrical Characteristics (Tc= 25°C unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A$, Reference 25°C	--	0.1	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=60V, V_{GS}=0V, T_a=25^\circ C$	--	--	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_a=125^\circ C$	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V$	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V$	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	13.5	18	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	--	2.5	V
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=20A$	18	--	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=30V$ $f=1.0MHz$	--	2050	--	pF
C_{oss}	Output Capacitance		--	158	--	
C_{rss}	Reverse Transfer Capacitance		--	120	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=20A, V_{DD}=30V$ $V_{GS}=10V, R_G=3.0\Omega$	--	7.5	--	ns
t_r	Rise Time		--	5.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	28.0	--	
t_f	Fall Time		--	5.5	--	
Q_g	Total Gate Charge	$I_D=20A, V_{DD}=30V$ $V_{GS}=10V$	--	50	--	nC
Q_{gs}	Gate to Source Charge		--	6	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	15	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	50	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	200	A
V_{SD}	Diode Forward Voltage	$I_S = 50A, V_{GS} = 0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S = 20A, T_J = 25^\circ C$	--	30	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s, V_{GS} = 0V$	--	40	--	nC
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta JA}$	Junction-to-Ambient	1.8	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: EAS condition : $T_J = 25^\circ C$, $V_{DD} = 30V, V_G = 10V, L = 0.5mH, R_g = 25\Omega$

^{a3}: $I_{SD} = 20A, di/dt \leq 100A/\mu s, V_{DD} \leq BV_{DS}$, Start $T_J = 25^\circ C$

Test Circuit and Waveform

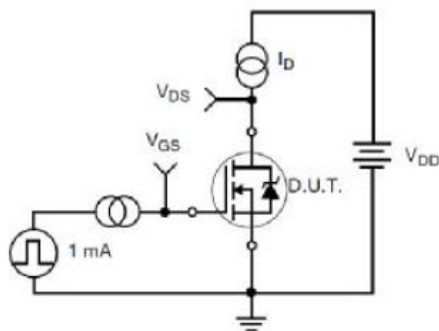


Figure 17. Gate Charge Test Circuit

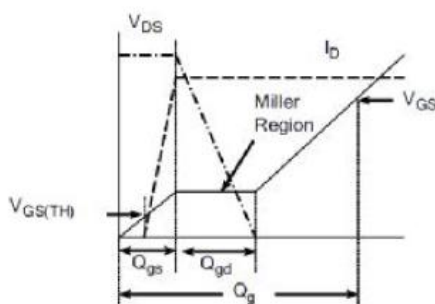


Figure 18. Gate Charge Waveform

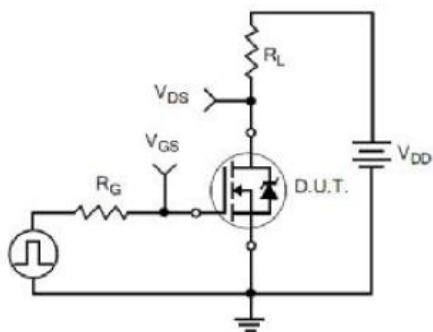


Figure 19. Resistive Switching Test Circuit

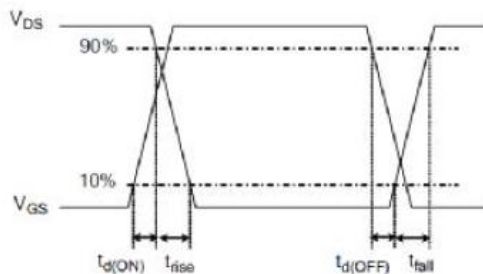


Figure 20. Resistive Switching Waveforms

Characteristics Curves

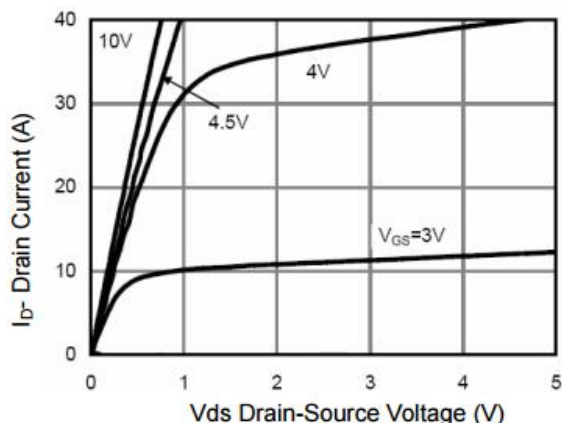


Figure 1 Output Characteristics

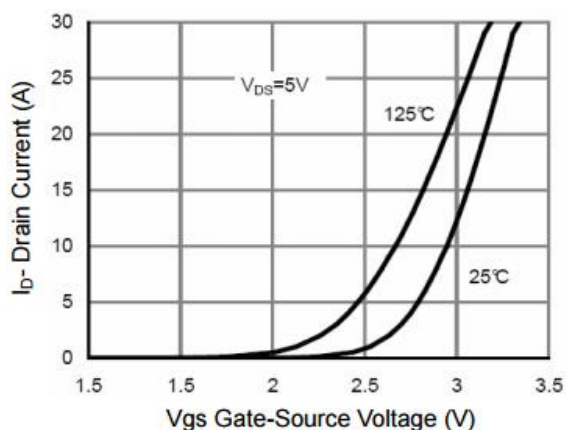


Figure 2 Transfer Characteristics

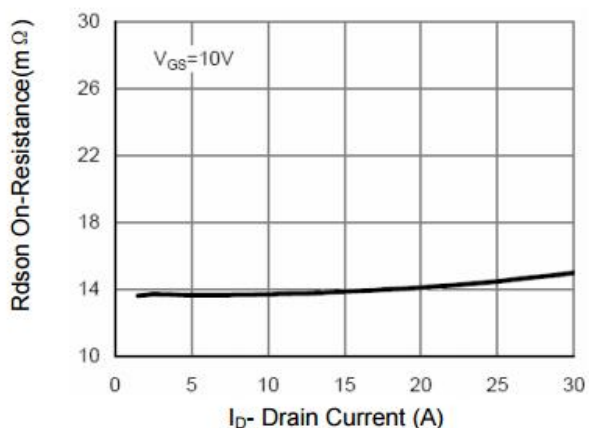


Figure 3 Rdson- Drain Current

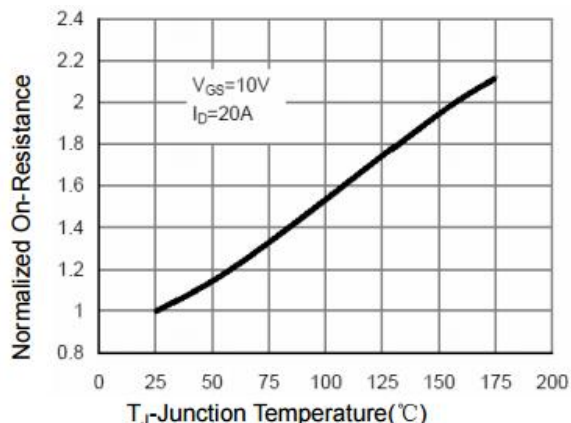


Figure 4 Rdson-Junction Temperature

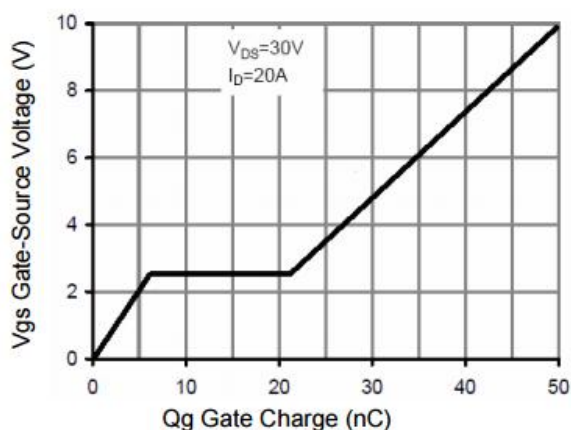


Figure 5 Gate Charge

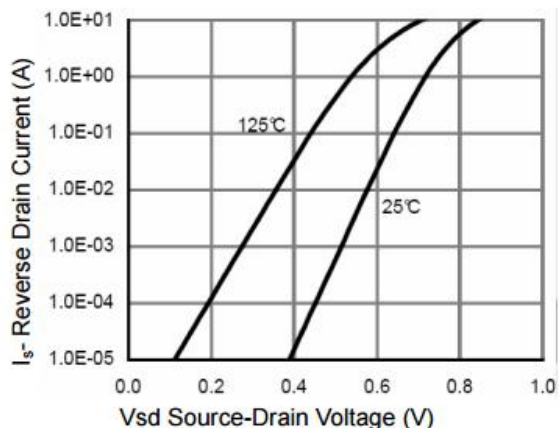


Figure 6 Source- Drain Diode Forward

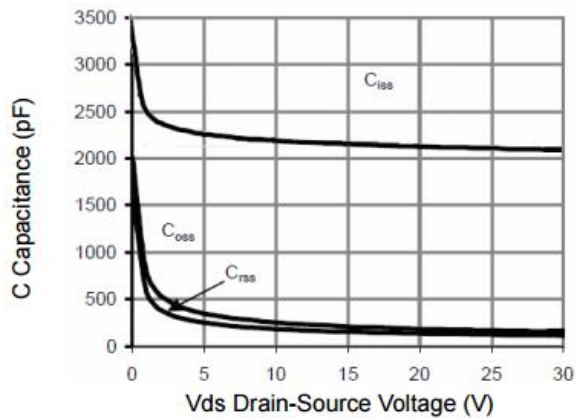


Figure 7 Capacitance vs V_{DS}

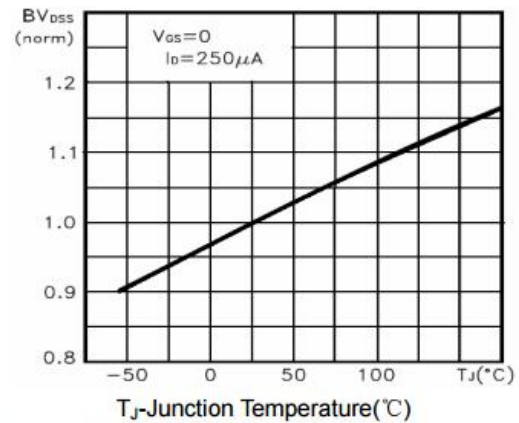


Figure 9 BV_{DSS} vs Junction Temperature

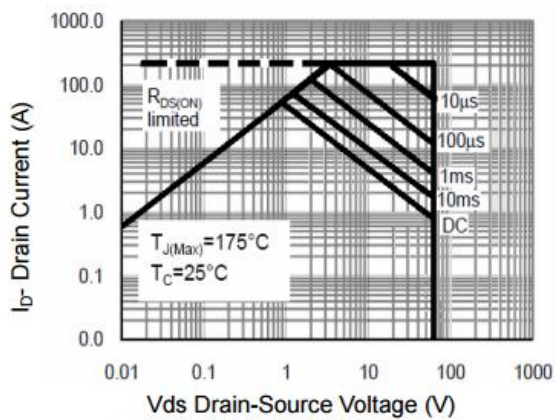


Figure 8 Safe Operation Area

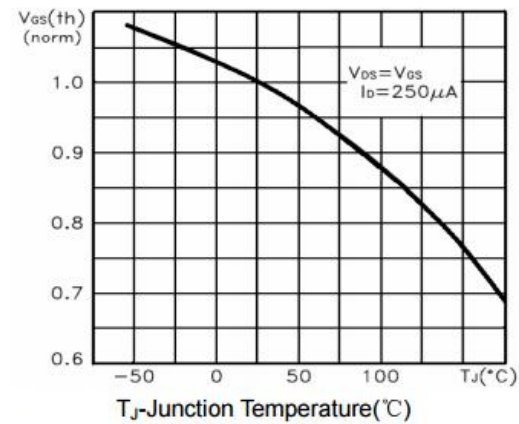


Figure 10 $V_{GS(th)}$ vs Junction Temperature

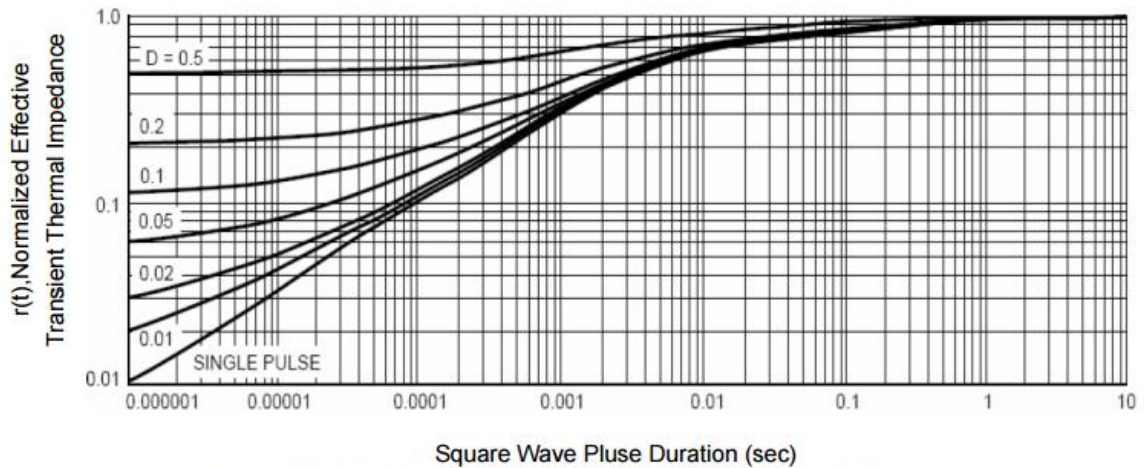


Figure 11 Normalized Maximum Transient Thermal Impedance